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(54) **POWER DEVICE WITH INTEGRATED SCHOTTKY DIODE AND METHOD FOR MAKING THE SAME**

(75) Inventor: **Donald R. Disney**, Cupertino, CA (US)

(73) Assignee: **Monolithic Power Systems, Inc.**, San Jose, CA (US)

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H01L 27/07 (2006.01)

H01L 29/808 (2006.01)

(52) **U.S. Cl.**

CPC **H01L 29/8725** (2013.01); **H01L 27/0727** (2013.01); **H01L 29/808** (2013.01); **H01L 29/872** (2013.01)

(58) **Field of Classification Search**

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USPC 257/272, 332, E29.021, E29.027, 257/E29.121, E29.258, E29.262, E29.318, 257/330, 333, 368; 438/570

See application file for complete search history.

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Primary Examiner — Stephen W Smoot

Assistant Examiner — Edward Chin

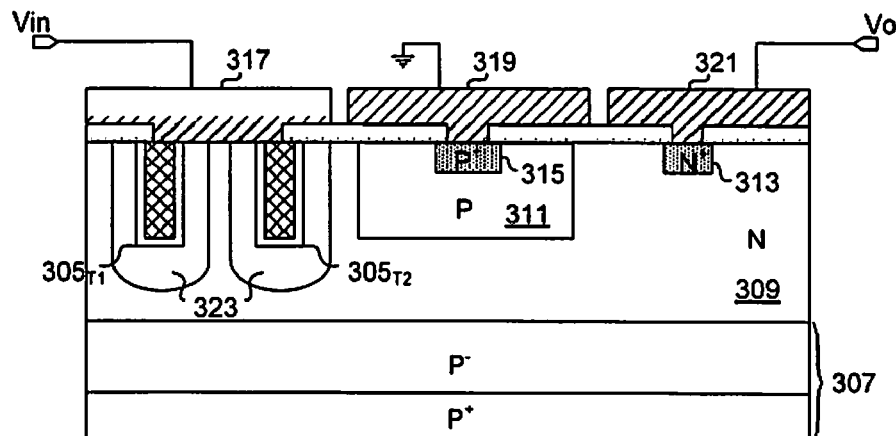
(74) *Attorney, Agent, or Firm* — Perkins Coie LLP

(57)

ABSTRACT

The present invention discloses a power device with integrated power transistor and Schottky diode and a method for making the same. The power device comprises a power transistor having a drain region, a Schottky diode in the drain region of the power transistor, and a trench-barrier near the Schottky diode. The trench-barrier is provided to reduce a reverse leakage current of the Schottky diode and minimizes the possibility of introducing undesired parasitic bipolar junction transistor in the power device.

10 Claims, 6 Drawing Sheets



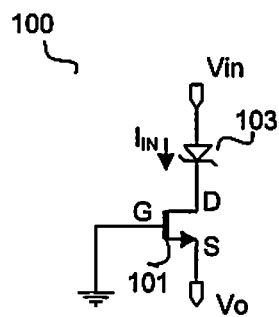


FIG. 1A

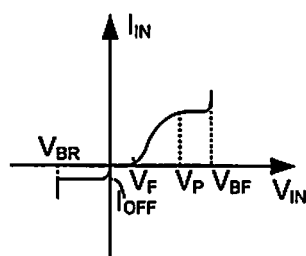


FIG. 1B

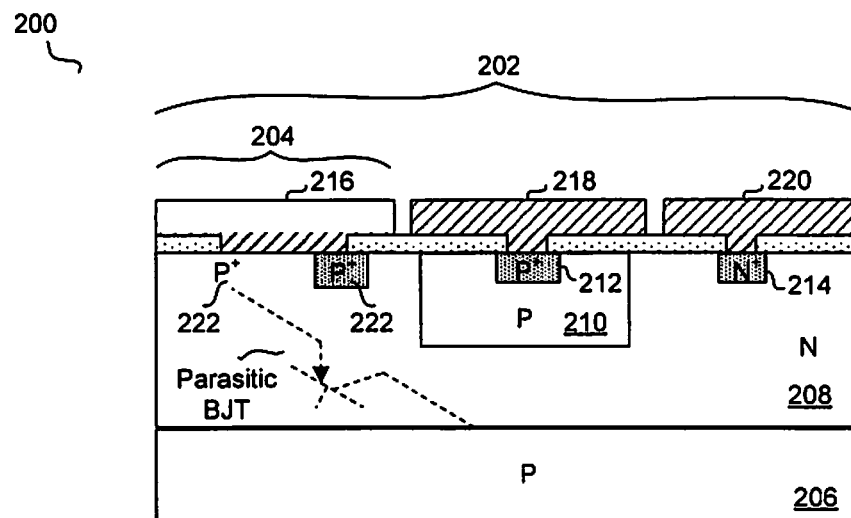


FIG. 2

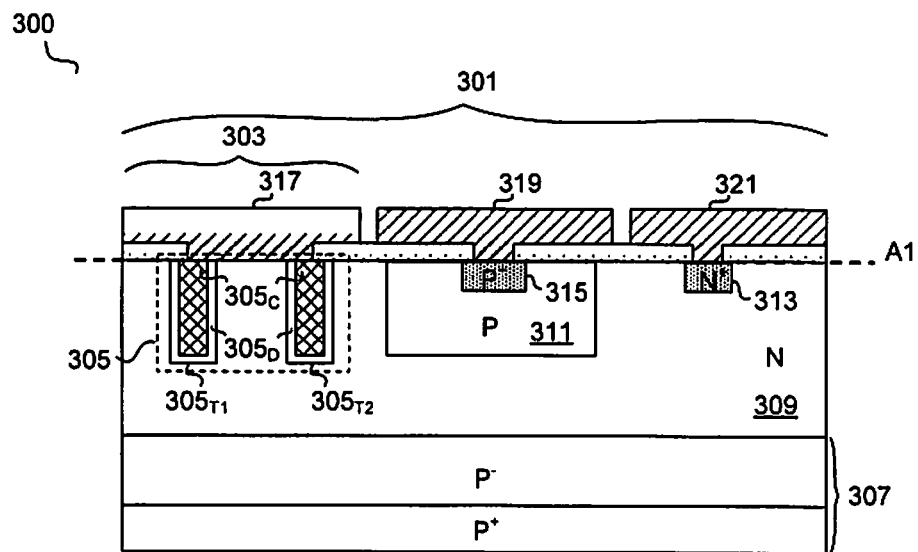


FIG. 3A

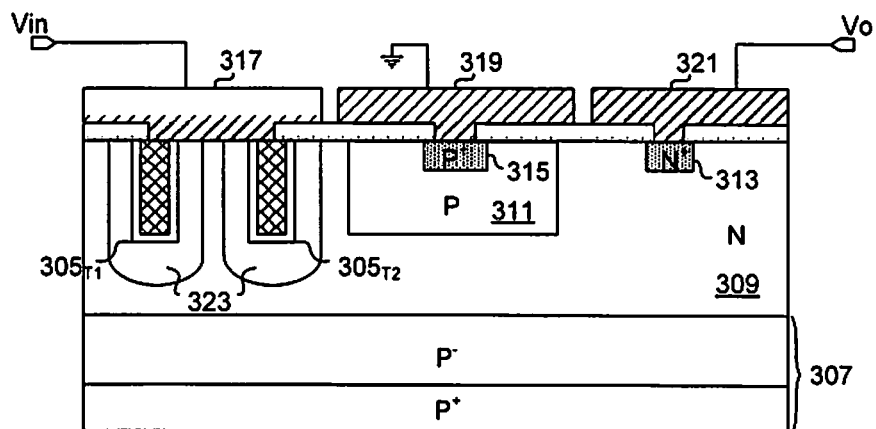


FIG. 3B

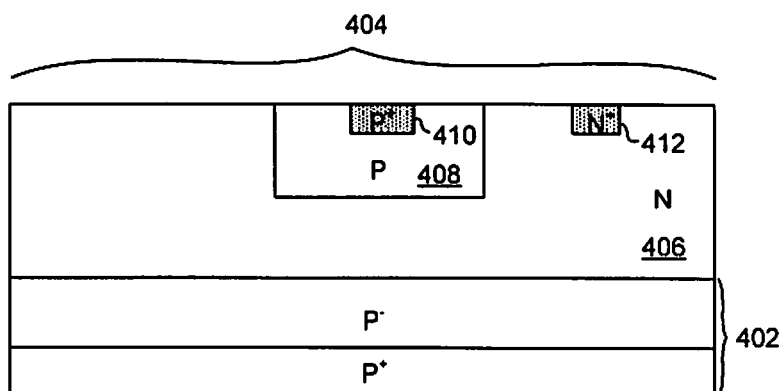


FIG. 4A

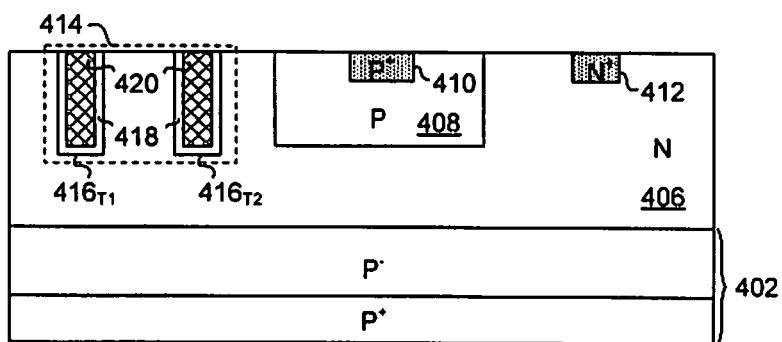


FIG. 4B

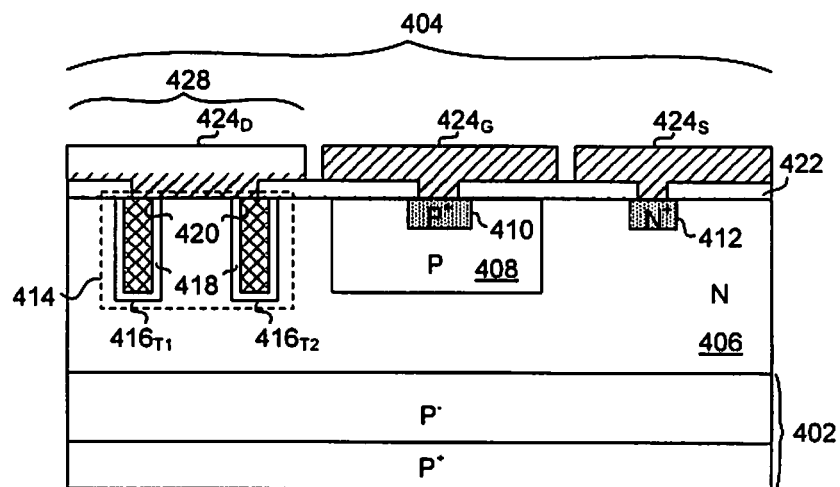
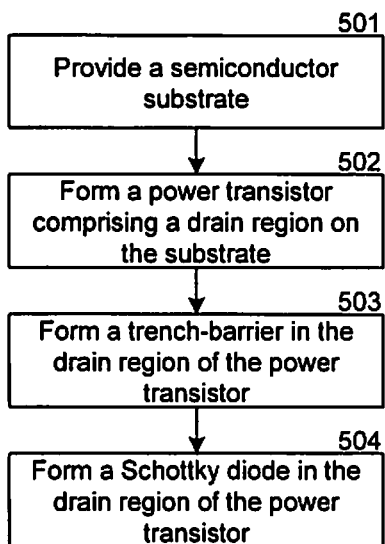


FIG. 4C

**FIG. 5**

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POWER DEVICE WITH INTEGRATED SCHOTTKY DIODE AND METHOD FOR MAKING THE SAME

TECHNICAL FIELD

This disclosure relates generally to semiconductor devices, and particularly relates to high-voltage junction field effect transistors with integrated Schottky diodes.

BACKGROUND

Power device comprising a power transistor and a Schottky diode integrated with the power transistor is often required in power management circuits. FIG. 1A illustrates a simple power conversion circuit **100** configured on the basis of a power device comprising a power transistor **101** and a Schottky diode **103** connected in series to convert an input voltage V_{in} to an output voltage V_o . The power transistor **101** comprises, for example, a junction field effect transistor (JFET) having a gate (G) connected to ground. Thus a complicated control circuit is not required. However, the JFET is a normally-ON device that conducts current in either direction from drain (D) to source (S) or from source (S) to drain (D). Therefore, without the Schottky diode **103**, when the output voltage V_o is higher than the input voltage V_{in} , a current flows reversely from V_o to V_{in} . The Schottky diode **103** is provided for blocking this reverse current flow.

FIG. 1B shows a diagram illustrating a current (I_{IN}) through Schottky diode **103** and JFET **101** as a function of V_{in} , assuming the gate and the source of JFET **101** are grounded. When the input voltage V_{in} is higher than a forward conduction voltage V_F of the Schottky diode **103**, the current I_{IN} flows from the input V_{in} to the output V_o through the forward biased Schottky diode **103** and the normally-ON JFET **101**. As V_{in} increases further, the JFET **101** may “pinch off” at a certain voltage (V_P) such that the current I_{IN} remains substantially constant for higher values of V_{in} . In a typical application, the output voltage V_o is not grounded, but rather is used to power a next-stage circuit. In such configuration, V_o rises with increasing V_{in} up to V_P , and then remains relatively constant. Thus, JFET **101** passes a current from V_{in} to the next-stage circuit while blocks high voltages (voltages higher than V_P) which may damage the next-stage circuit. When V_{in} reaches a forward breakdown voltage (V_{BF}) of the JFET **101**, a large current flows from V_{in} to the gate of JFET **101** and/or to V_o . When V_{in} is negative with respect to V_o , the current I_{IN} turns to be an off-state leakage current (T_{OFF}) flowing from V_o to V_{in} . When the negative V_{in} voltage exceeds a breakdown voltage (V_{BR}) of the Schottky diode **103**, a high current flows from V_o to V_{in} .

FIG. 2 illustrates a sectional view of a prior art power device **200** integrating a JFET **202** and a Schottky diode **204**. The power device **200** has a p-type substrate **206**. An n-type well region **208** is formed on the p-type substrate **206**. The JFET **202** and the Schottky diode **204** share the same p-type substrate **206** and the same n-type well region **208**. A p-type doped region **210** is provided in the n-type well region **208** to form a gate region of the JFET **202** and a p⁺ heavily doped region **212** is formed in the p-type doped region **210** to function as an ohmic contact for the gate region **210**. The n-type well region **208** at the left side of the gate region **210** forms a drain region of the JFET **202** and the n-type well region **208** at the right side of the gate region **210** forms a source region of the JFET **202**. An n⁺ heavily doped region **214** is provided in the n-well region **208** at the right side of the gate region **210** to form an ohmic contact of the source region. A drain metal

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216, a gate metal **218** and a source metal **220** functioning respectively as a drain electrode D, a gate electrode G and a source electrode S of the combined power device **200** are formed to respectively contact the drain region, the p⁺ heavily doped region **212** and the n⁺ heavily doped region **214**.

The Schottky diode **204** comprises a cathode sharing the n-type well region **208** and an anode sharing the drain metal **216**. The Schottky diode **204** further comprises p⁺ heavily doped regions **222** provided on both sides of Schottky diode **204**. P⁺ regions **222** are used to form a merged PN Schottky (MPS) diode, which reduces a reverse leakage current of the Schottky diode **204**. Without the p⁺ heavily doped region **222**, the reverse leakage current of the Schottky diode **204** may be unacceptably high.

However, the p⁺ heavily doped region **222** may cause a problem when the power device **200** is in ON state and the Schottky diode **204** is forward biased. In fact, there exists a parasitic bipolar junction transistor (BJT) which uses the p⁺ heavily doped region **222**, the n-type well region **208** and the p-type substrate **206** as an emitter, a base and a collector, respectively. At high forward current, the junction between the p⁺ heavily doped region **222** and the n-type well region **208** may be forward biased, causing the parasitic bipolar transistor to turn ON. In this case, carriers may be injected into the substrate **206** and disturb the operation of other circuits that are integrated with the power device **200**, which is undesirable.

SUMMARY

In one embodiment, a power device, comprises a semiconductor substrate; a power transistor formed in the semiconductor substrate, wherein the power transistor comprises a drain region, a source region, a gate region, and a drain metal coupled to the drain region; a trench-barrier formed in the drain region of the power transistor, wherein the trench-barrier comprises a first trench and a second trench separated by a portion of the drain region; and a Schottky diode formed between the first and the second trenches, wherein the Schottky diode has an anode comprising the drain metal and a cathode comprising a portion of the drain region of the power transistor.

In one embodiment, a power device comprises a semiconductor substrate of a first conductivity type; a well region of a second conductivity type formed in the substrate; a gate region of the first conductivity type formed in the well region; a first trench and a second trench formed in the well region, wherein the first trench and the second trench are separated by a portion of the well region; and a drain metal contacting the portion of the well region between the first and the second trenches to form a metal-semiconductor contact.

In one embodiment, a method of forming a power device integrating a power transistor and a Schottky diode comprises providing a semiconductor substrate; forming the power transistor in the semiconductor substrate, wherein, forming the power transistor comprises forming a drain region, a gate region and a source region in the semiconductor substrate; forming a trench-barrier in the drain region of the power transistor, wherein forming the trench-barrier comprises forming a first trench and a second trench separated by a portion of the drain region; and forming the Schottky diode in the drain region of the power transistor, wherein forming the Schottky diode comprises forming a drain metal to contact the portion of the drain region between the first and the second trenches of the trench-barrier.

In one embodiment, a method of manufacturing a power device comprises providing a semiconductor substrate of a

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first conductivity type; forming a well region of a second conductivity type on the substrate; forming a gate region of the first conductivity type in the well region; forming a first trench and a second trench in the well region, wherein the first trench and the second trench are separated by a portion of the well region; and forming a drain metal to contact the portion of the well region between the first and the second trenches.

BRIEF DESCRIPTION OF THE DRAWINGS

The following detailed description of the embodiments of the present disclosure can best be understood when read in conjunction with the following drawings, in which the features are not necessarily drawn to scale but rather are drawn as to best illustrate the pertinent features.

FIG. 1A shows a schematic diagram of a prior art power conversion circuit **100**.

FIG. 1B shows a diagram illustrating a current-voltage relationship of the prior art power conversion circuit in FIG. 1A.

FIG. 2 shows a sectional view of a prior art power device **200** integrating a JFET and a merged PN Schottky diode.

FIG. 3A shows a sectional view of a power device **300** in accordance with an embodiment of the present invention.

FIG. 3B shows an exemplary configuration of the power device **300** in FIG. 3A when it is used to convert an input voltage V_{in} to an output voltage V_o .

FIGS. 4A to 4C show sectional views of a fabrication process of a power device in accordance with an embodiment of the present invention.

FIG. 5 shows a flow chart illustrating a method of forming a power device in accordance with an embodiment of the present invention.

The use of the same reference label in different drawings indicates the same or like components.

DETAILED DESCRIPTION

Various embodiments of the present invention will now be described. In the following description, some specific details, such as example circuits and example values for these circuit components, are included to provide a thorough understanding of embodiments. One skilled in the relevant art will recognize, however, that the technology can be practiced without one or more specific details, or with other methods, components, materials, etc. In other instances, well-known structures, materials, processes or operations are not shown or described in detail to avoid obscuring aspects of the technology.

The terms “left,” “right,” “in,” “out,” “front,” “back,” “up,” “down,” “top,” “atop,” “bottom,” “over,” “under,” “above,” “below” and the like in the description and the claims, if any, are used for descriptive purposes and not necessarily for describing permanent relative positions. It is to be understood that the terms so used are interchangeable under appropriate circumstances such that embodiments of the present invention described herein are, for example, capable of operation in other orientations than those illustrated or otherwise described herein. The term “coupled,” as used herein, is defined as directly or indirectly connected in an electrical or non-electrical manner.

A power device integrating a power transistor and a Schottky diode with a trench-barrier is disclosed. In accordance with an embodiment of the present invention, the power device comprises a semiconductor substrate; a power transistor formed in the semiconductor substrate, wherein the power transistor comprises a drain region, a source region, a gate

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region, and a drain metal coupled to the drain region; a trench-barrier formed in the drain region of the power transistor, wherein the trench-barrier comprises a first trench and a second trench separated by a portion of the drain region; and a Schottky diode formed between the first and the second trenches, wherein the Schottky diode has an anode comprising the drain metal and a cathode comprising a portion of the drain region of the power transistor.

In one embodiment, the first and the second trenches are filled with a conductive material, and the conductive material is separated from the drain region of the power transistor by a dielectric material.

In other embodiment, the first trench and the second trench have sidewalls and bottoms lined with a dielectric material.

In still other embodiment, the drain metal contacts the conductive material of the first and the second trenches.

According to various embodiments of the present invention, the Schottky diode with a trench-barrier has a rather small reverse leakage current and blocks current from flowing in an undesired direction in the power device while allow current flow in a desired direction when a relatively low series voltage that is higher than the forward conduction voltage (about 0.3V) of the Schottky diode is additionally applied to the power device. Thus, the power device having an integrated Schottky diode with a trench-barrier in accordance with various embodiments of the present invention conducts a current in a desired direction and blocks a reverse current in an undesired direction. In addition, the power device in accordance with various embodiments of the present invention does not comprise a parasitic bipolar junction transistor as the prior art power device of FIG. 1. Therefore, the power device integrating a power transistor and a Schottky diode with a trench-barrier according to the present invention greatly reduces or eliminates the potential problem of carrier injection into the substrate which may disturb the operation of other circuitry integrated with the power device.

FIG. 3A illustrates a sectional view of a power device **300** in accordance with an embodiment of the present invention. In the example of FIG. 3A, the power device **300** comprises a JFET **301**, a Schottky diode **303** and a trench-barrier **305**. In one embodiment, power device **300** has a p-type substrate **307** that may comprise a p^+ substrate layer and a p^- epitaxial layer. Power device **300** further has an n-type well region **309** atop the p-type substrate **307**. N-type well region **309** may have a p-type doped region **311**. It can be understood that, p-type doped region **311** may function as a gate region of JFET **301**, n-type well region **309** at the left side of p-type doped region **311** may function as a drain region of JFET **301**, and n-type well region **309** at the right side of p-type doped region **311** may function as a source region of JFET **301**.

In one embodiment, n-type well region **309** at the right side of p-type doped region **311** may further have an n^+ heavily doped region **313** near its top surface **A1**. N^+ heavily doped region **313** may function as an ohmic contact for the source region of JFET **301**. P-type doped region **311** may further have a p^+ heavily doped region **315** near the top surface **A1**. P^+ heavily doped region **315** may function as an ohmic contact for the gate region of JFET **301**. Power device **300** further has a drain metal **317**, a gate metal **319** and a source metal **321** functioning respectively as a drain electrode **D**, a gate electrode **G** and a source electrode **S** of power device **300** and contacting the drain region, the p^+ heavily doped region **315** and the n^+ heavily doped region **313**, respectively.

JFET **301** and Schottky diode **303** share the same p-type substrate **307** and the same n-type well region **309**. Schottky diode **303** comprises a cathode sharing the n-type well region

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309 and an anode sharing the drain metal **317** so that a metal-semiconductor contact is formed.

Trench-barrier **305** is formed near the Schottky diode **303** for blocking a reverse leakage current of the Schottky diode **303**. Trench-barrier **305** comprises a first trench **305_{T1}** and a second trench **305_{T2}** formed in the n-type well region **309**, wherein, the first trench **305_{T1}** and the second trench **305_{T2}** are respectively at the left side and the right side of Schottky diode **303**. The first trench **305_{T1}** and the second trench **305_{T2}** are lined with a dielectric material **305_D** on their sidewalls and bottoms, and are filled with a conductive material **305_C** adjacent the dielectric material **305_D**. Conductive material **305_C** is coupled to the drain metal **317**. In one embodiment, conductive material **305_C** partly contacts the drain metal **317**.

In one embodiment, dielectric material **305_D** may comprise silicon dioxide. In one embodiment, conductive material **305_C** may comprise doped polysilicon.

FIG. 3B shows an exemplary configuration of the power device **300** when it is used to convert an input voltage V_{in} to an output voltage V_o . The drain metal **317** is coupled to V_{in} , the gate metal **319** is coupled to ground and the source metal **321** is coupled as an output terminal for V_o . When the input voltage V_{in} is higher than a forward conduction voltage of the Schottky diode **303**, power device **300** starts to conduct a current flowing from the drain to the source of JFET **301** (i.e., from V_{in} to V_o). Since trench-barrier **305** is formed in trenches **305_{T1}** and **305_{T2}**, and conductive material **305_C** which fills the trenches **305_{T1}** and **305_{T2}** is isolated from the n-well region **309** by dielectric material **305_D**, and thus reducing the formation of a parasitic bipolar junction transistor in power device **300**, and further, carrier injection into the n-well region **309** from conductive material **305_C** is prevented. Thus, power device **300** integrating a JFET and a Schottky diode with trench-barrier may not have the potential problem of injecting carriers into the substrate when power device **300** is in conduction state and the Schottky diode **303** is forward biased.

When the output voltage V_o is higher than the input voltage V_{in} , the Schottky diode **303** shifts from forward biasing to reverse biasing. Since there are only electrons participating in the current flow, the reverse recovery time of the Schottky diode **303** is very short. As the cathode-to-anode voltage of the Schottky diode **303** becomes more positive with V_o increasing, depletion regions **323** start to form in the n-well region **309** around the first and the second trenches **305_{T1}** and **305_{T2}**. According to an embodiment, the space between the trenches **305_{T1}** and **305_{T2}** is designed to allow the depletion regions **323** to be merged at a relatively low voltage (e.g. 1–10V). Once the depletion regions **323** are merged, the voltage across the Schottky diode **303** remains relatively constant, and the Schottky diode **303** is shielded from further increase in the output voltage V_o .

Therefore, trench-barrier **305** not only greatly reduces the reverse leakage current of Schottky diode **303**, but also supports a higher breakdown voltage of Schottky diode **303** in a relatively small cathode area. Moreover, trench barrier **305** helps to minimize or eliminate the forming possibility of a parasitic bipolar junction transistor in power device **300** and significantly reduces or eliminates carriers that may be injected into the substrate of power device **300**.

In one embodiment, power device **300** may have asymmetric blocking capability, which means that power device **300** may support much more voltage from drain electrode **317** to source electrode **321** and/or gate electrode **319** than from source electrode **321** and/or gate electrode **317** to drain electrode **317**. To achieve this asymmetric blocking capability, the length of the portion of N-well region **309** between trench

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barrier **305** and gate region **311** is substantially longer than the length of the portion of N-well region **309** between gate region **311** and source region **313**.

Although in the embodiments described based on FIGS. 3A and 3B power device **300** is disclosed as having a JFET **301** integrated with the Schottky diode **303** and the trench-barrier **305**. In various embodiments of the present invention, power device **300** may have other types of power transistors such as metal oxide semiconductor field effect transistor (MOSFET) and bipolar junction transistor etc., instead of the JFET **301**, integrated with the Schottky diode **303** and the trench-barrier **305**.

FIGS. 4A to 4C show a fabrication process of a power device with integrated power transistor and trench-barrier Schottky diode in accordance with an embodiment of the present invention.

As shown in FIG. 4A, at a first step, a semiconductor substrate **402** is originally provided and in the following steps a power transistor **404** is fabricated on the semiconductor substrate **402**. In one embodiment, the semiconductor substrate **402** may comprise a p-type substrate. In one embodiment, the p-type substrate may comprise a p⁺ substrate layer and a p⁺ epitaxial layer formed on the p⁺ substrate layer. In one embodiment, the power transistor **404** may comprise an n-channel JFET. Forming the n-channel JFET **404** may comprise: forming an n-type well region **406** on the semiconductor substrate **402**; and forming a p-type gate region **408** in the n-type well region **406**. In one embodiment, forming the n-channel JFET **404** may further comprise: forming a p⁺ heavily doped region **410** in the p-type gate region **408**; and forming an n⁺ heavily doped region **412** in the n-type well region **406** at one side of the gate region **408**.

In the next step, as illustrated in FIG. 4B, a trench-barrier **414** is formed in the n-type well region **406**. In one embodiment, forming the trench-barrier **414** may comprise: forming a first trench **416_{T1}** and a second trench **416_{T2}** in the n-type well region **406** at the other side of the gate region **408**; forming a dielectric material **418** on the sidewalls and the bottoms of the first and the second trenches **416_{T1}** and **416_{T2}**; and filling the first and the second trenches **416_{T1}** and **416_{T2}** with a conductive material **420**. In one embodiment, dielectric material **418** may comprise silicon dioxide. In one embodiment, conductive material **420** may comprise doped polysilicon.

In the next step, as illustrated in FIG. 4C, a dielectric layer **422** is formed on the n-well region **406** and is etched to expose the p⁺ heavily doped region **410**, the n⁺ heavily doped region **412**, the n-well region **406** between the first trench **416_{T1}** and the second trench **416_{T2}**, and a portion of the conductive material **420**. Then, a metal layer **424** is applied on the dielectric layer **422** and etched into a drain metal **424_D**, a gate metal **424_G** and a source metal **424_S**, which respectively functions as a drain electrode, a gate electrode and a source electrode of the power transistor **404**. Drain metal **424_D**, gate metal **424_G** and source metal **424_S** respectively contacts the exposed n-well region **406** and conductive material **420**, the exposed p⁺ heavily doped region **410** and the exposed n⁺ heavily doped region **412**. At this point, a Schottky diode **428** is also formed between the first trench **416_{T1}** and the second trench **416_{T2}**, using the drain metal **424_D** as an anode and the n-well region **406** as a cathode.

The fabrication process illustrated in FIGS. 4A to 4C is for illustration purpose and does not limit the present invention to the precise embodiments described. In other embodiments, the semiconductor substrate **402** may comprise an n-type substrate and the power transistor **404** may comprise a p-channel JFET. In still other embodiments, the power tran-

sistor **404** may comprise other types of power transistors such as MOSFET or BJT ect. Moreover, well known manufacturing steps, processes, materials and dopants etc. are not described in detail in the present disclosure to avoid obscuring aspects of the technology. Those skilled in the art should understand that the steps described in the embodiment shown may be implemented in different orders and are not limited to the embodiment described.

FIG. 5 shows a flow chart illustrating a method of forming a power device integrating a power transistor and a Schottky diode. The method comprises: providing a semiconductor substrate at step **501**; forming a power transistor on the substrate at step **502**, wherein forming the power transistor comprises forming a drain region, a gate region and a source region on the substrate; forming a trench-barrier in the drain region of the power transistor at step **503**; and forming a Schottky diode in the drain region of the power transistor at step **504**.

In an embodiment, forming the power transistor at step **502** comprises forming a drain region, a gate region and a source region on the substrate. In an embodiment, forming the trench-barrier at step **503** comprises forming a first trench and a second trench separated by a portion of the drain region of the power transistor, wherein the first and the second trenches have sidewalls and bottoms. In an embodiment, forming the Schottky diode at step **504** comprises forming a drain metal to contact the portion of the drain region between the first trench and the second trench of the trench-barrier.

In an embodiment, forming the trench-barrier at step **503** further comprises: forming a dielectric material on the sidewalls and bottoms of the first and the second trenches; and filling the first and the second trenches with a conductive material.

Although the present disclosure takes an N-channel JFET for example to explain the structures and manufacturing processes of a power device with integrated power transistor and Schottky diode, this is not intended to be limiting and persons of skill in the art will understand that the structures and principles taught herein also apply to P-channel JFET, N-channel/P-channel MOSFET and to other types of semiconductor materials and devices as well. While poly-silicon is preferred for filling the trenches used in embodiments of the present invention, the embodiments are not limited to this choice of conductor and other types of materials (e.g., metals, other semiconductors, semi-metals, and/or combinations thereof) that are compatible with other aspects of the device manufacturing process may also be used. Thus, the terms “poly-filled” and “poly-silicon filled” are intended to include such other materials and material combinations in addition to silicon.

From the foregoing, it will be appreciated that specific embodiments of the technology have been described herein for purposes of illustration, but that various modifications may be made without deviating from the disclosure. Many of the elements of one embodiment may be combined with other embodiments in addition to or in lieu of the elements of the other embodiments. Accordingly, the disclosure is not limited except as by the appended claims.

I claim:

1. A power device, comprising: a semiconductor substrate; a power transistor formed in the semiconductor substrate, wherein the power transistor comprises a drain region, a source region, a gate region, and a drain metal coupled to the drain region; a trench-barrier formed in the drain region of the power transistor, wherein the trench-barrier comprises a first trench and a second trench separated by a portion of the drain region; and wherein the first and the second trenches are filled

with a conductive material, and wherein the conductive material is separated from the drain region of the power transistor by a dielectric material, and wherein the drain metal contacts the conductive material of the first and the second trenches; and a Schottky diode formed between the first and the second trenches, wherein the Schottky diode has an anode comprising the drain metal and a cathode comprising a portion of the drain region of the power transistor, and wherein the trench-barrier is configured to block a reverse leakage current of the Schottky diode.

2. The power device of claim 1, wherein the first and the second trenches have sidewalls and bottoms lined with the dielectric material.

3. A power device, comprising: a semiconductor substrate of a first conductivity type; a well region of a second conductivity type formed in the substrate; a gate region of the first conductivity type formed in the well region; a first trench and a second trench formed in the well region, wherein the first trench and the second trench are separated by a portion of the well region; and wherein the first and the second trenches are filled with a conductive material, and wherein the conductive material is separated from the well region by a dielectric material; and a drain metal contacting the portion of the well region between the first and the second trenches to form a metal-semiconductor contact functioning as a Schottky diode, wherein the drain metal contacts the conductive material of the first and the second trenches; and wherein the first and the second trenches filled with the conductive material are configured to block a reverse leakage current of the Schottky diode.

4. The power device of claim 3, wherein the first and the second trenches have sidewalls and bottoms lined with the dielectric material.

5. The power device of claim 3, wherein the well region comprises a drain region and a source region, and wherein the gate region is disposed laterally between the drain region and the source region.

6. The power device of claim 5, further comprising a gate ohmic contact region of the first conductivity type in the gate region; and a source ohmic contact region of the second conductivity type in the source region.

7. A method of forming a power device integrating a power transistor and a Schottky diode, comprising: providing a semiconductor substrate; forming the power transistor in the semiconductor substrate, wherein forming the power transistor comprises forming a drain region, a gate region and a source region in the semiconductor substrate; forming a trench-barrier in the drain region of the power transistor, wherein forming the trench-barrier comprises forming a first trench and a second trench separated by a portion of the drain region; and wherein the trench-barrier is configured to block a reverse leakage current of the Schottky diode; and forming the Schottky diode in the drain region of the power transistor, wherein forming the Schottky diode comprises forming a drain metal to contact the portion of the drain region between the first and the second trenches of the trench-barrier; and wherein the first and the second trenches have sidewalls and bottoms, and wherein forming the trench-barrier further comprises: forming a dielectric material on the sidewalls and bottoms of the first and the second trenches; and filling the first and the second trenches with a conductive material; and wherein forming the drain metal further comprises forming an electrical contact between the drain metal and the conductive material of the first and the second trenches.

8. A method of manufacturing a power device, comprising: providing a semiconductor substrate of a first conductivity type; forming a well region of a second conductivity

type on the substrate; forming a gate region of the first conductivity type in the well region; forming a first trench and a second trench in the well region, wherein the first trench and the second trench are separated by a portion of the well region; forming a drain metal to contact the portion of the well region between the first and the second trenches so as to form a Schottky diode; and wherein the first and the second trenches have sidewalls and bottoms, and wherein forming the first and the second trenches further comprises: forming a dielectric material on the sidewalls and bottoms of the first and the second trenches; and filling the first and the second trenches with a conductive material, and wherein the first and the second trenches filled with the conductive material are configured to block a reverse leakage current of a Schottky diode; and wherein forming the drain metal further comprises forming an electrical contact between the drain metal and the conductive material of the first and the second trenches.

9. The method of claim **8**, further comprising: forming a drain region and a source region in the well region, wherein the drain region and the source region are laterally separated by the gate region.

10. The method of claim **9**, further comprising: forming a gate ohmic contact region of the first conductivity type in the gate region; and forming a source ohmic contact region of the second conductivity type in the source region.

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